Silicon NPN Power Transistors 2SC2429

DESCRIPTION

·With TO-3 package
·High voltage ,high speed
·Wide area of safe operation

APPLICATIONS

·High speed switching
·Converters and inverters

Fig.1 s implified o utline (TO-3) a nd s ymbol

PINNING (See Fig.2)

PIN DE	SCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(Ta=□)

SYMBOL P	ARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	450	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		15	A
I_{CM} C	ollector current-Peak		20	A
I_B	Base current		5	A
P_T	Total power dissipation	T_C=25□	150	W
T_j	Junction temperature		175	□
T_{stg} S	torage temperature		-65~175	□

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CHARACTERISTICS

Tj=25□ u nless otherwise specified

SYMBOL P	ARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=1A ; R_{BE}=∞	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	7			V
V_{CEsat} C	ollector-emitter saturation voltage	I_C=10A; I_B=2A		0.45	1.0	V
V_{BEsat} B	ase-emitter saturation voltage	I_C=10A; I_B=2A		1.2	2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=450V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=10A ; V_{CE}=5V 10		15	40	
f_T	Transition frequency	I_C=2A ; V_{CE}=10V,f=10MHz		35		MHz
C_{OB} C	ollector output capacitance	I_E=0 ; V_{CB}=10V,f=1MHz		230		pF
Switching times						
t_r	Rise time	V_{CC}=150V,I_C=10A I_{B1}=-I_{B2}=2A		0.15	0.5	μs
t_{stg} S	torage time			1.20	2.5	μs
t_f	Fall time		0.	10	0.3	μs

PACKAGE OUTLINE

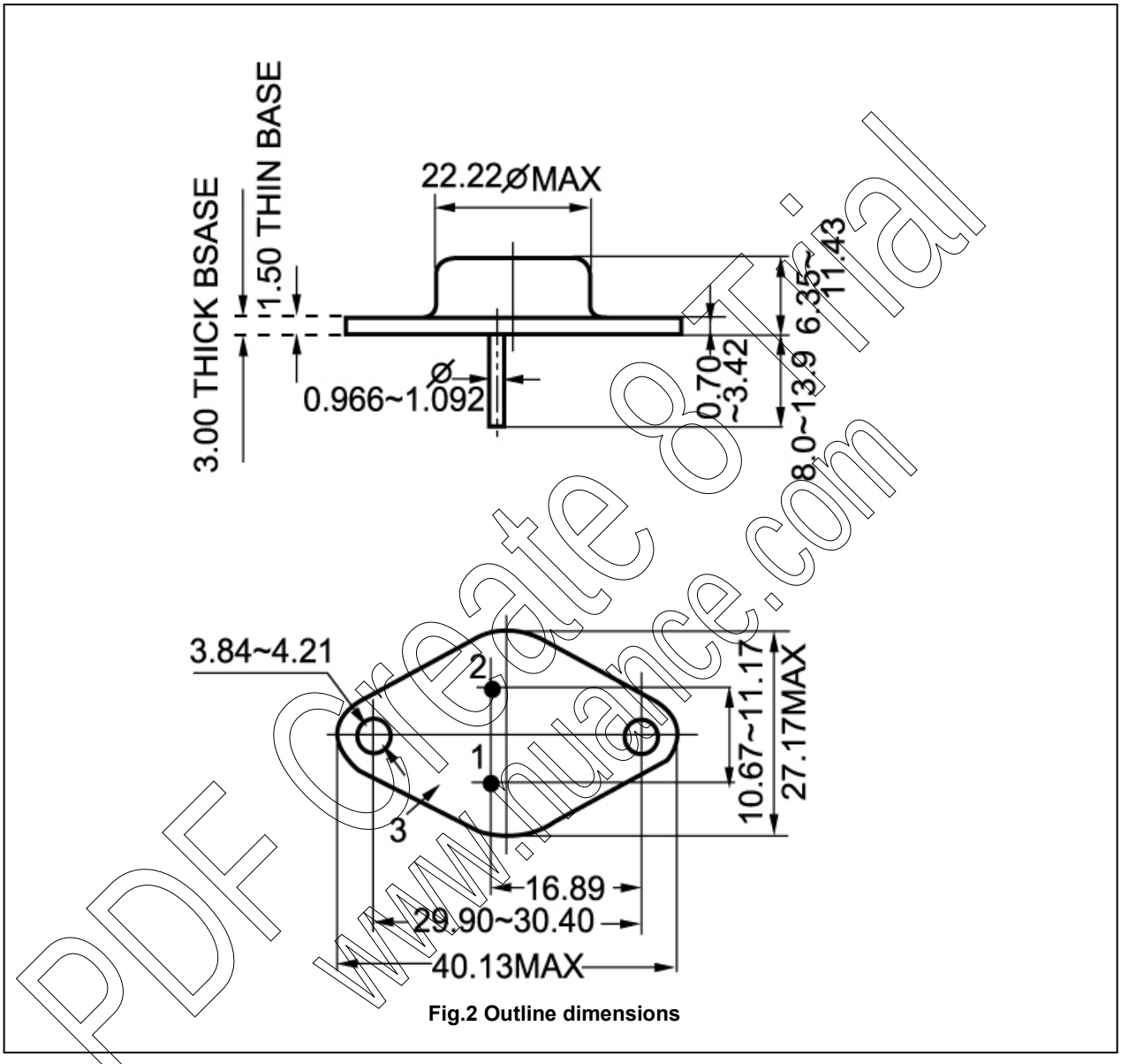

Fig.2 Outline dimensions